

A METHOD OF MANUFACTURING A Laterally
DIFFUSED METAL OXIDE SEMICONDUCTOR DEVICE

ABSTRACT OF THE DISCLOSURE

5 A method of manufacturing a laterally diffused metal oxide
semiconductor (LDMOS) device, and an integrated circuit associated
therewith. The method includes forming a lightly-doped
source/drain region with a first dopant, the lightly-doped
source/drain region located between first and second isolation
structures. The method further includes creating a gate over the
lightly-doped source/drain region. In one advantageous embodiment
of the present invention, the method further includes diffusing a
second dopant at least partially across the lightly-doped
source/drain region and under the gate to form a first portion of
a channel.